

Theory of semiconductor quantum dot cavity-QED:

-- Addressing entanglement, non-equilibrium phonon, and photon distributions --

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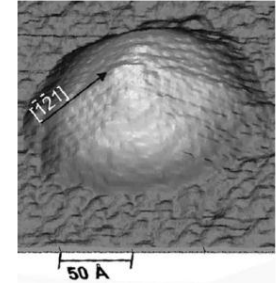
OUTLINE

Folie: 2

Bayreuth: Seminar SS 2012

I: Semiconductor Quantum Dot

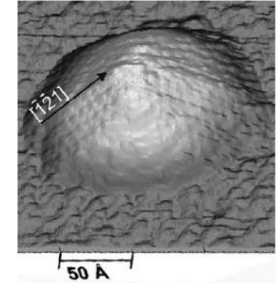
- Semiconductor physics and heterostructures
- Quantum Dot Hamiltonian and equation of motion approach



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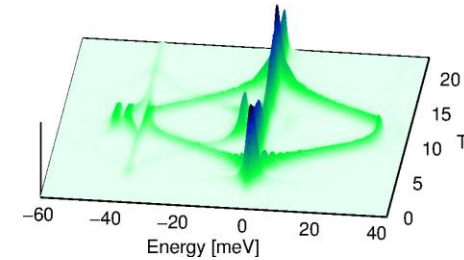
I: Semiconductor Quantum Dot

- Semiconductor physics and heterostructures
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II: Quantum Dot as a Two-Level System

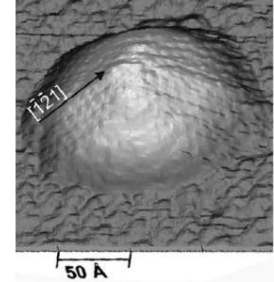
- Time-resolved phonon-assisted Mollow triplet
- Proposal for a phonon laser
- Photon-loss and induced quantum feedback



OUTLINE

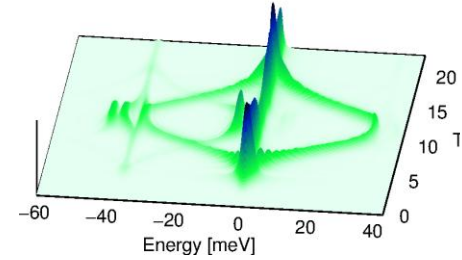
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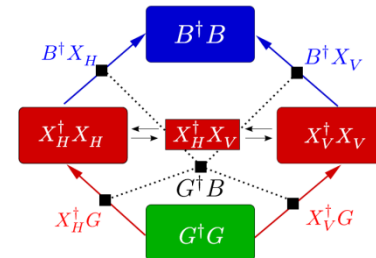
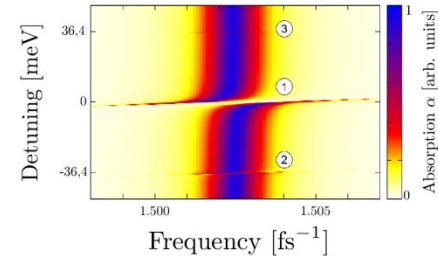
II: Quantum Dot as a Two-Level System

- Time-resolved phonon-assisted Mollow triplet
- Proposal for a phonon laser
- Photon-loss and induced quantum feedback



III: Quantum Dot as a Four-Level System

- Entangled photons: Pure dephasing does not matter
- Entangled photons: Multi-phonon scattering beyond 70K
- Strongly coupled cavity-QED: Crosscorrelation



(i) semiconductor quantum dot

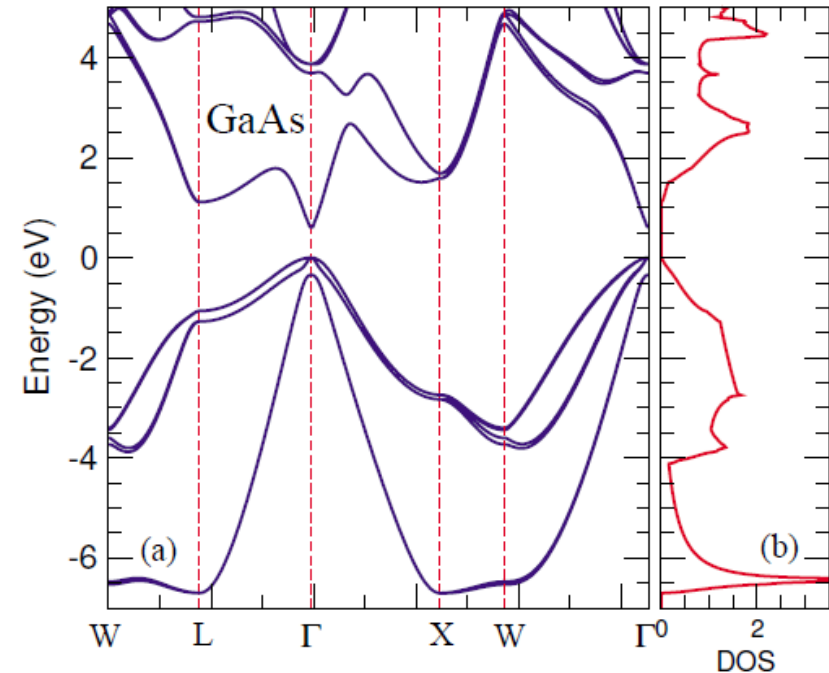
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Semiconductor structures – effective mass approximation

Bayreuth: Seminar SS 2012

$$\mathcal{H}_0 = -\frac{\hbar^2}{2m_0}\Delta + V_{\text{lat}}(\mathbf{r})$$

Bandstructure of GaAs:
 Parabolic structure of lowest conduction and highest valence band

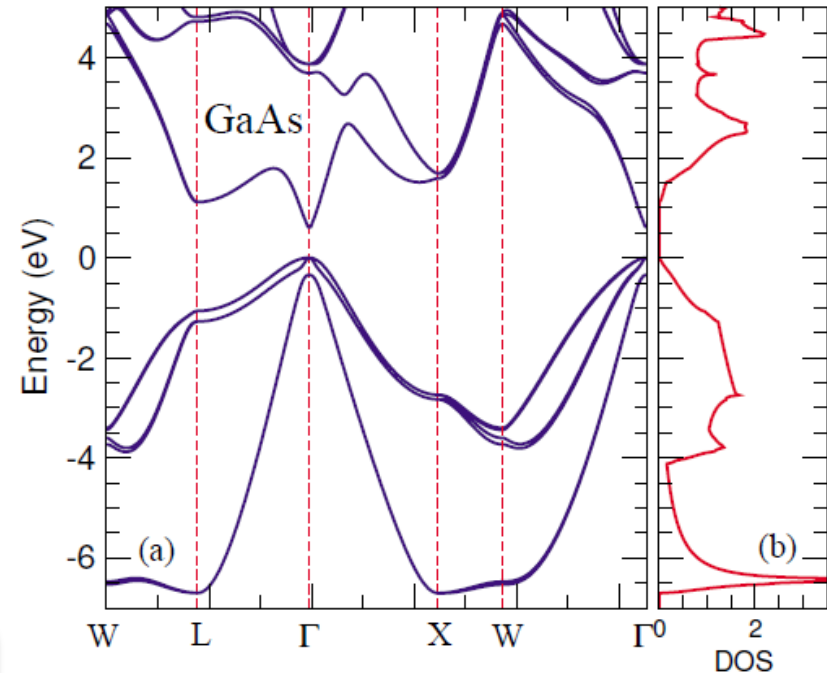


Semiconductor structures – effective mass approximation

Bayreuth: Seminar SS 2012

$$\mathcal{H}_0 = -\frac{\hbar^2}{2m_0}\Delta + V_{\text{lat}}(\mathbf{r})$$

Bandstructure of GaAs:
 Parabolic structure of lowest conduction
 and highest valence band



$$E_n(\mathbf{k}) \approx E_n(0) + \frac{\hbar^2 k^2}{2m_n^*} \quad \text{with} \quad \frac{1}{m_n^*} = \frac{1}{\hbar^2} \left. \frac{\partial^2 E_n(\mathbf{k})}{\partial k^2} \right|_{\mathbf{k}_{\Gamma=0}}$$



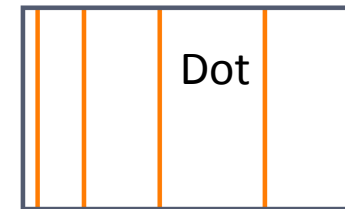
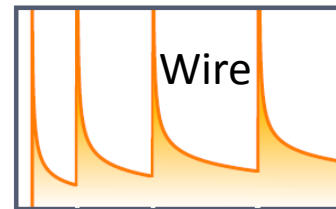
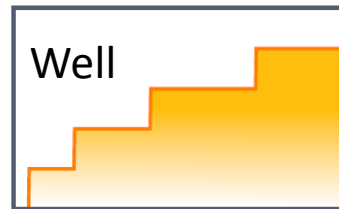
Mixing semiconductors with different
 band gaps: nanostructures

Semiconductor Nanostructures and second quantization

Folie: 8

Confinement potential:
 Geometry, Size,
 Material specifics

$$\left[-\frac{\hbar^2}{2m_n^*} \Delta + V_{\text{conf}}(\mathbf{r}) \right] \xi_n(\mathbf{r}) = \varepsilon_n \xi_n(\mathbf{r}) \quad \text{with} \quad \varepsilon_n = E - E_n(0)$$

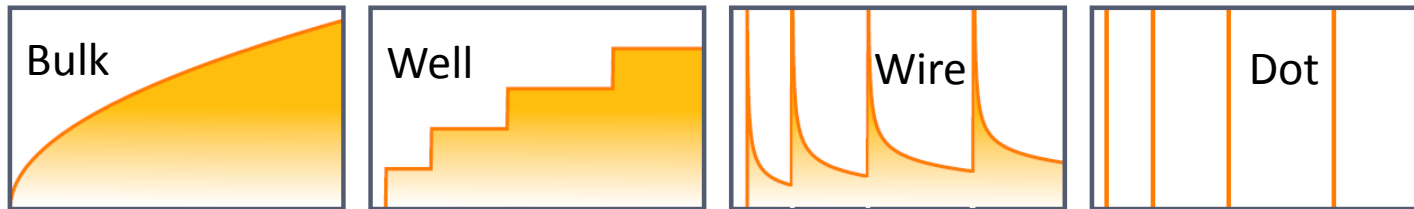


Semiconductor Nanostructures and second quantization

Folie: 9

Confinement potential:
 Geometry, Size,
 Material specifics

$$\left[-\frac{\hbar^2}{2m_n^*} \Delta + V_{\text{conf}}(\mathbf{r}) \right] \xi_n(\mathbf{r}) = \varepsilon_n \xi_n(\mathbf{r}) \quad \text{with} \quad \varepsilon_n = E - E_n(0)$$



$$\varphi_n(\mathbf{r}) = u_{n, \mathbf{k} \approx 0}(\mathbf{r}) \xi_n(\mathbf{r})$$

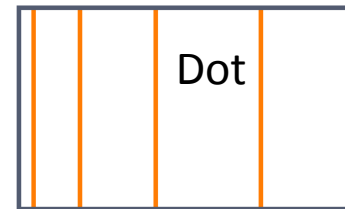
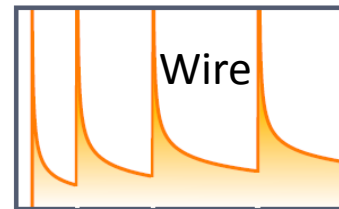
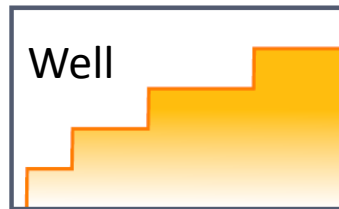
$$\hat{\Psi}(\mathbf{r}) = \sum_n \varphi_n(\mathbf{r}) \hat{a}_n,$$

$$\hat{\Psi}^\dagger(\mathbf{r}) = \sum_n \varphi_n^*(\mathbf{r}) \hat{a}_n^\dagger$$

Semiconductor Nanostructures and second quantization

Confinement potential:
Geometry, Size,
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Microscopic calculated
Wave function for
2nd quantization

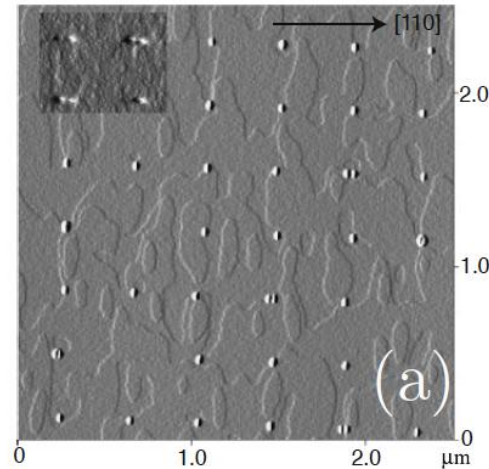
$$\begin{aligned} \hat{H}_0^c &= \int d^3 r \hat{\Psi}^\dagger(\mathbf{r}) \left(-\frac{\hbar^2}{2m_0} \Delta + V_{\text{lat}}(\mathbf{r}) + V_{\text{conf}}(\mathbf{r}) \right) \hat{\Psi}(\mathbf{r}) \\ &= \sum_n \varepsilon_n \hat{a}_n^\dagger \hat{a}_n. \end{aligned}$$

Semiconductor quantum dots

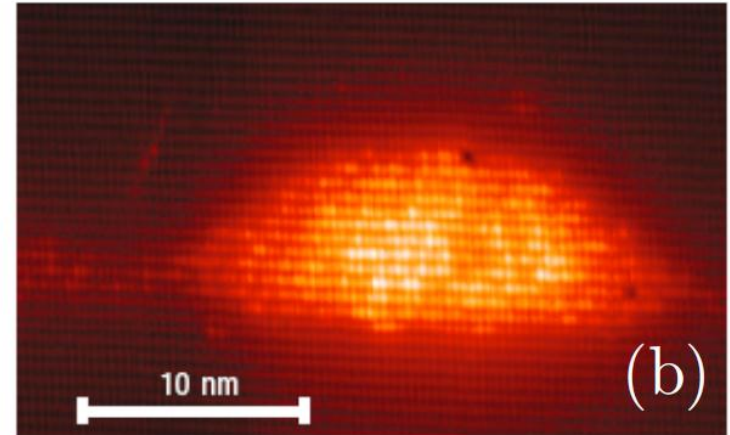
Quantum dots:
An artificial atom



Discrete energy levels
→ Optical properties by design
→ Electrical pumping possible



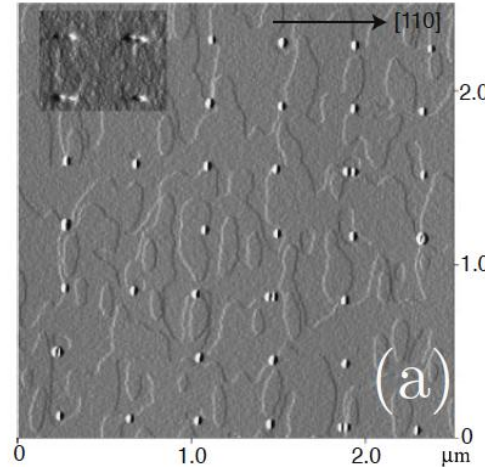
Atkinson et al., Jpn. J. Appl. Phys. 45 (2006)



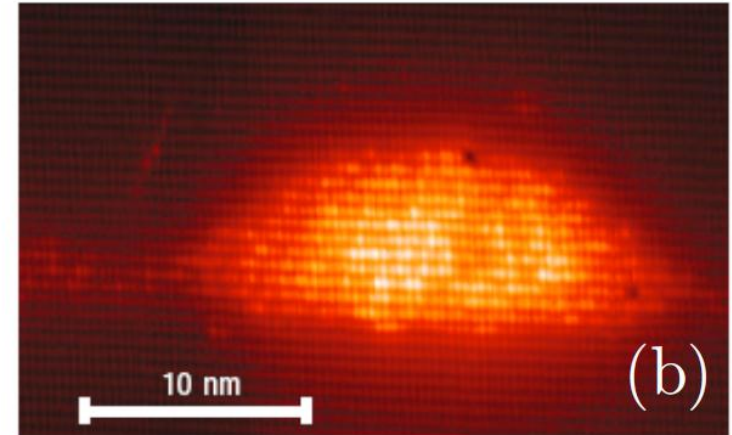
Shields, Nat. Photonics, 221 (2007)

Semiconductor quantum dots

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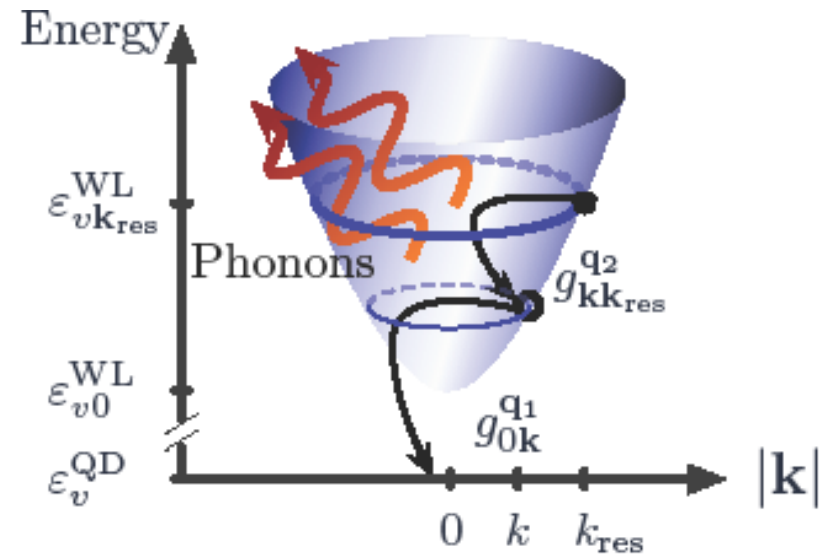


Atkinson et al., Jpn. J. Appl. Phys. 45 (2006)



Shields, Nat. Photonics, 221 (2007)

Discrete energy levels
 → Optical properties by design
 → Electrical pumping possible
 But:
 Semiconductor environment (wetting layer, phonons) leads to dephasing!

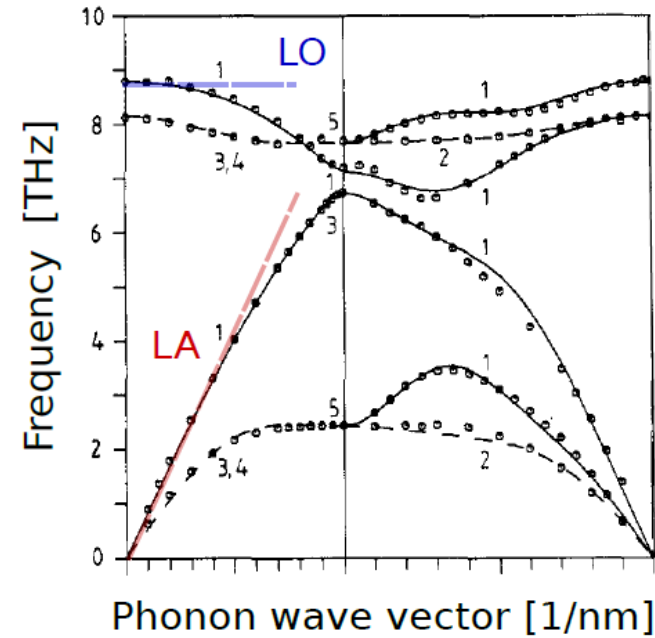


Dephasing mechanism in a semiconductor QD

Pure dephasing:

→ Deformation (LA) potential¹

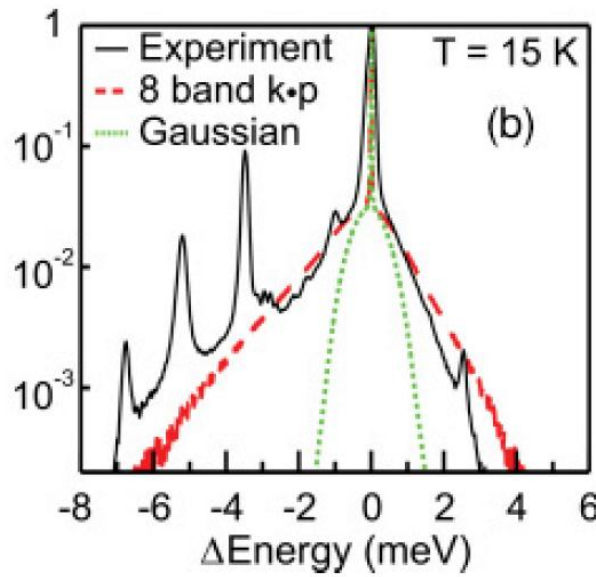
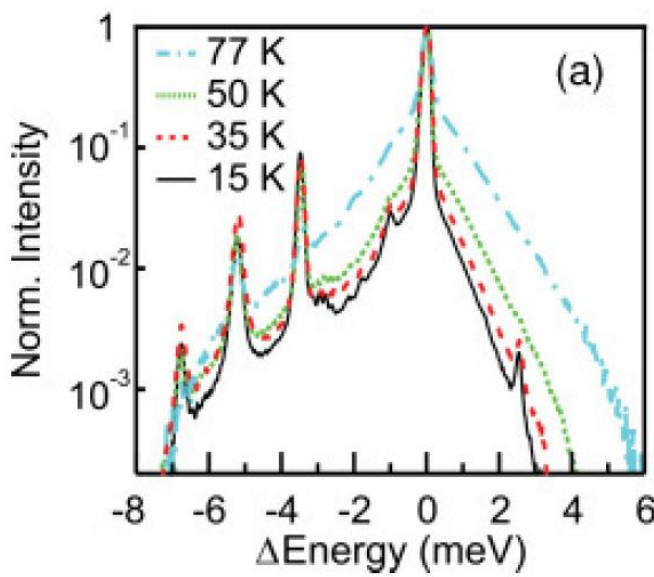
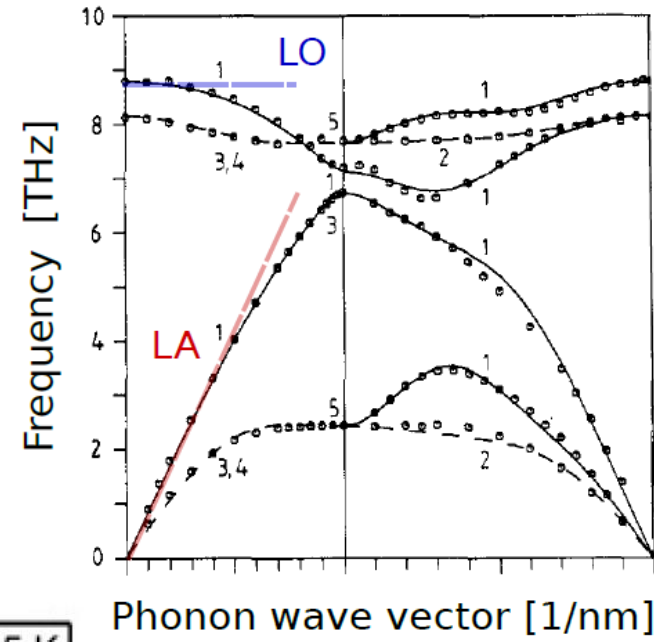
$$g_{\text{LA},q}^{\lambda\mu,3\text{D}} = \delta_{\lambda,\mu} \sqrt{\frac{\hbar q}{2\rho c_s V}} D_\lambda$$



Dephasing mechanism in a semiconductor QD

Pure dephasing:
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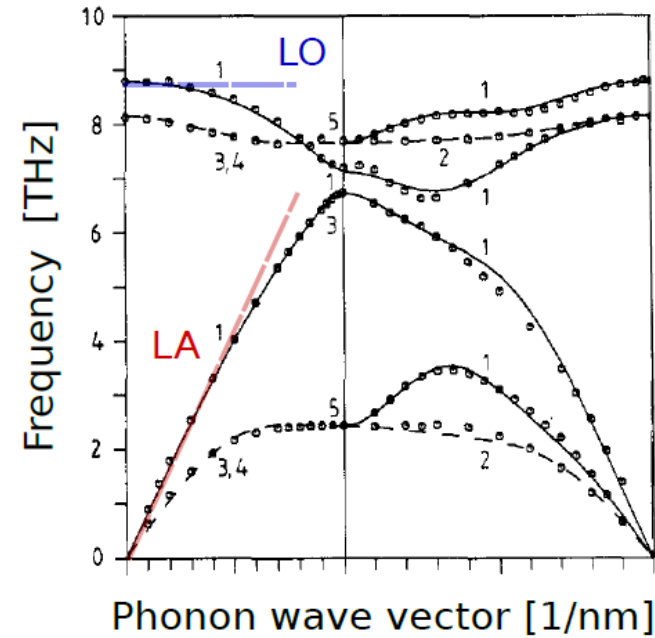
¹PRB **83**, 041304(R) (2011)

Dephasing mechanism in a semiconductor QD

Pure dephasing:

→ Fröhlich (LO)
potential¹

$$g_{\text{LO},q}^{\lambda\mu,3\text{D}} = \frac{1}{q} \sqrt{\frac{e_0^2 \hbar \omega_{\text{LO}}}{2 \epsilon_0 V} \left(\frac{1}{\epsilon_\infty} - \frac{1}{\epsilon_{\text{st}}} \right)}$$



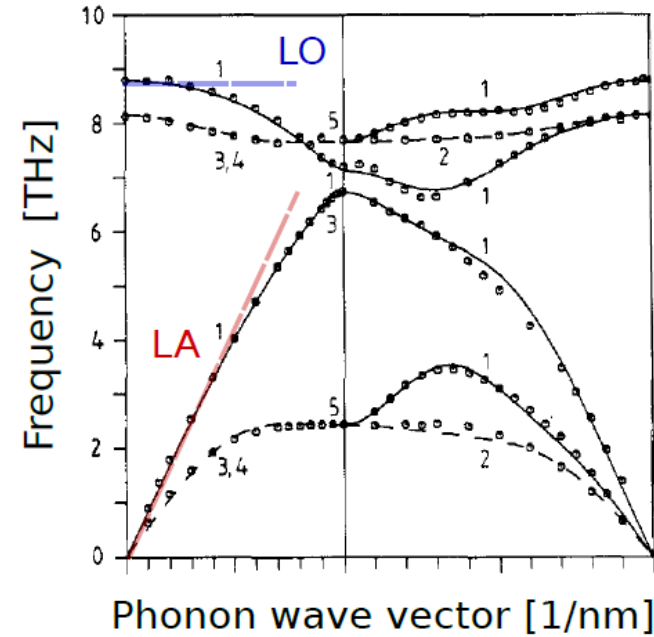
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Dephasing mechanism in a semiconductor QD

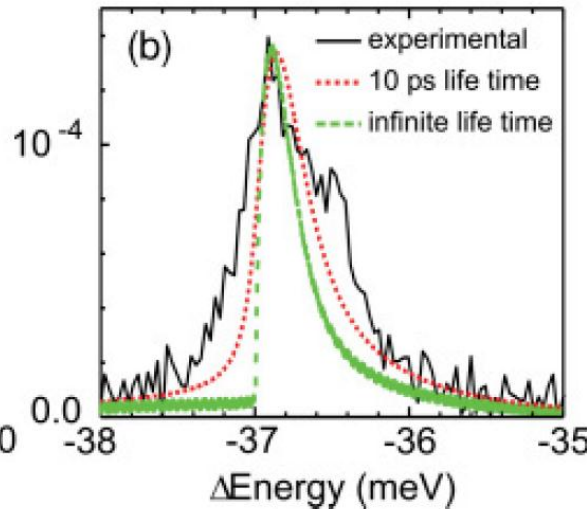
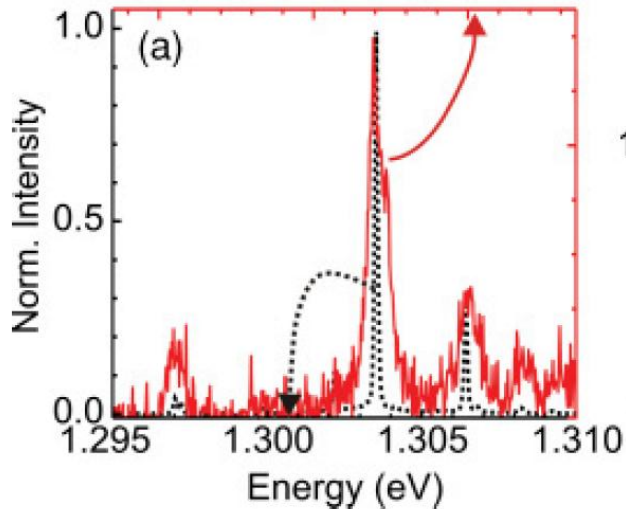
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Energy (eV) shifted by 36.5 meV
1.260 1.265 1.270



¹PRB **83**, 041304(R) (2011)

Goal

GOAL

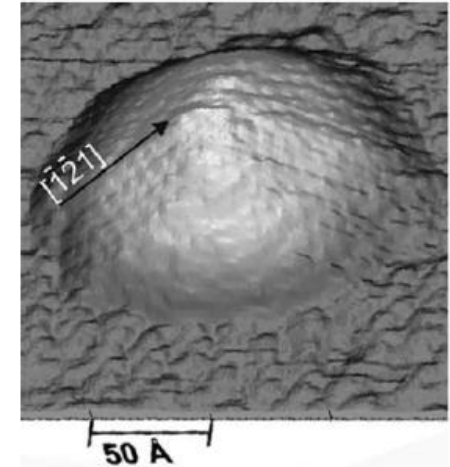
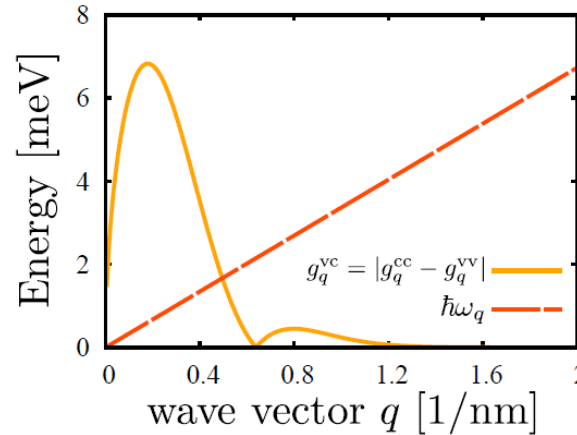
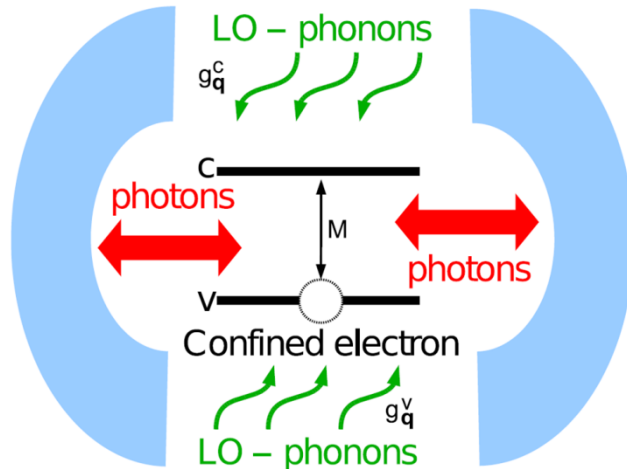


Developing a theoretical framework to find advantageous features of the semiconductor environment

(i) semiconductor quantum dot

- Semiconductor physics and heterostructures
- Quantum Dot Hamiltonian and equation of motion approach

Semiconductor QD cavity-QED Hamiltonian



$$H = H_{\text{el}} + H_{\text{phonon}} + H_{\text{photon}} + H_{\text{laser}}$$

$$H_{\text{el}} = \hbar \sum_i \omega_i a_i^\dagger a_i + \hbar \sum_{ijlm} V_{lm}^{ij} a_i^\dagger a_j^\dagger a_l a_m$$

$$H_{\text{phonon}} = \hbar \sum_{\mathbf{q}} \omega_{\mathbf{q}} b_{\mathbf{q}}^\dagger b_{\mathbf{q}} + \hbar \sum_{i,j,\mathbf{q}} g_{\mathbf{q}}^{ij} a_i^\dagger a_j b_{\mathbf{q}}^\dagger + \text{H.c.}$$

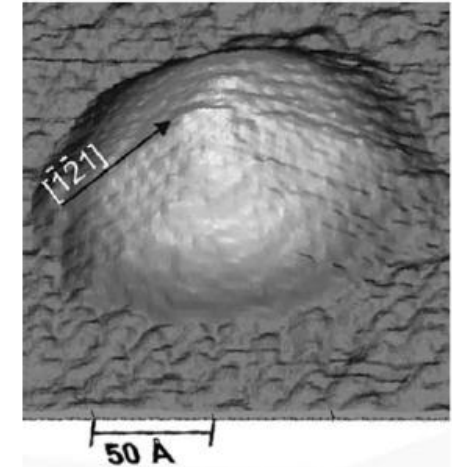
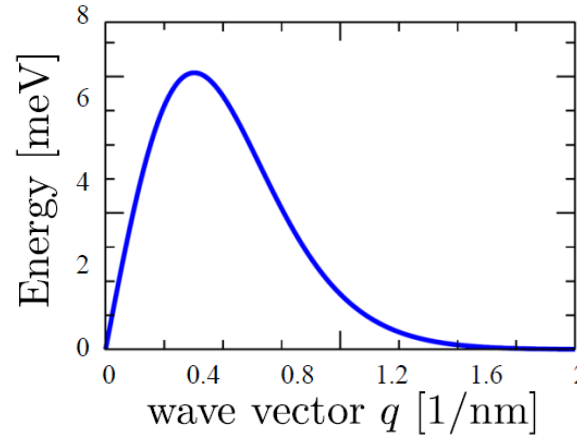
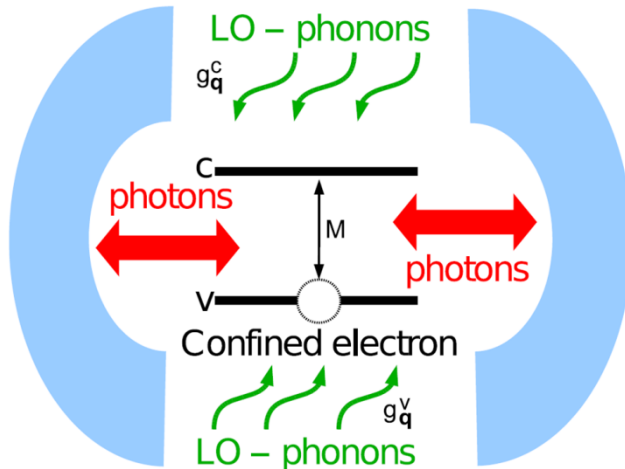
$$H_{\text{photon}} = \hbar \sum_{\mathbf{k}} \omega_{\mathbf{k}} c_{\mathbf{k}}^\dagger c_{\mathbf{k}} + \hbar \sum_{i,j,\mathbf{q}} M_{\mathbf{k}}^{ij} a_i^\dagger a_j c_{\mathbf{k}}^\dagger + \text{H.c.}$$

$$H_{\text{laser}} = \hbar \sum_{i,j} \Omega^{ij} a_i^\dagger a_j + \text{H.c.}$$

Semiconductor QD cavity-QED Hamiltonian

Folie: 20

Bayreuth: Seminar SS 2012



Marquez et al., Appl.Phys.Lett. 78 (2001)

$$H = H_{\text{el}} + H_{\text{phonon}} + H_{\text{photon}} + H_{\text{laser}}$$

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Solving LO-phonon QD cavity-QED without factorization

Folie: 21

Bayreuth: Seminar SS 2012

for every possible combination of
phonon, photon, and electron operators
for example a two-level system:

$$G_{m,n}^{p,s} := a_v^\dagger a_v c^{\dagger p} c^s \bar{b}^{\dagger m} \bar{b}^n$$

$$E_{m,n}^{p,s} := a_c^\dagger a_c c^{\dagger p} c^s \bar{b}^{\dagger m} \bar{b}^n$$

$$T_{m,n}^{p,s} := a_v^\dagger a_c c^{\dagger p} c^s \bar{b}^{\dagger m} \bar{b}^n$$

Solving LO-phonon QD cavity-QED without factorization

Using product rule for operators: $\partial_t \left(a_c^\dagger a_c c^\dagger c b_q^\dagger b_q \right) = \left(\partial_t a_c^\dagger a_c c^\dagger c \right) b_q^\dagger b_q + c^\dagger c \left(\partial_t a_c^\dagger a_c b_q^\dagger b_q \right)$

and generalized commutation relations:

$$[A, F(B)] = [A, B]F'(B)$$

for every possible combination of phonon, photon, and electron operators for example a two-level system:

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and generalized commutation relations:

$$[A, F(B)] = [A, B]F'(B)$$

for every possible combination of phonon, photon, and electron operators for example a two-level system:

and

their dynamics, e.g.

$$G_{m,n}^{p,s} := a_v^\dagger a_v c^{\dagger p} c^s \bar{b}^{\dagger m} \bar{b}^n$$

$$E_{m,n}^{p,s} := a_c^\dagger a_c c^{\dagger p} c^s \bar{b}^{\dagger m} \bar{b}^n$$

$$T_{m,n}^{p,s} := a_v^\dagger a_c c^{\dagger p} c^s \bar{b}^{\dagger m} \bar{b}^n$$

$$\partial_t \langle T_{m,n}^{p,s} \rangle =$$

$$\begin{aligned} &= -i [\omega_{cv} - (p-s)\omega_0 - (m-n)\omega_{LO} - i(p+s)\kappa - i\gamma] \langle T_{m,n}^{p,s} \rangle \\ &\quad - ip M \langle E_{m,n}^{p-1,s} \rangle - iM (\langle E_{m,n}^{p,s+1} \rangle - \langle G_{m,n}^{p,s+1} \rangle) - i\Omega(t) (\langle E_{m,n}^{p,s} \rangle - \langle G_{m,n}^{p,s} \rangle) \\ &\quad - i \langle T_{m,n+1}^{p,s} \rangle - i \langle T_{m+1,n}^{p,s} \rangle + i m g_v \langle T_{m-1,n}^{p,s} \rangle - i n g_c \langle T_{m,n-1}^{p,s} \rangle, \end{aligned}$$

General set of equations of motion

For example, in the case of LO-phonon assisted vacuum Rabi oscillations ($E_{00}^{11} = 0$):

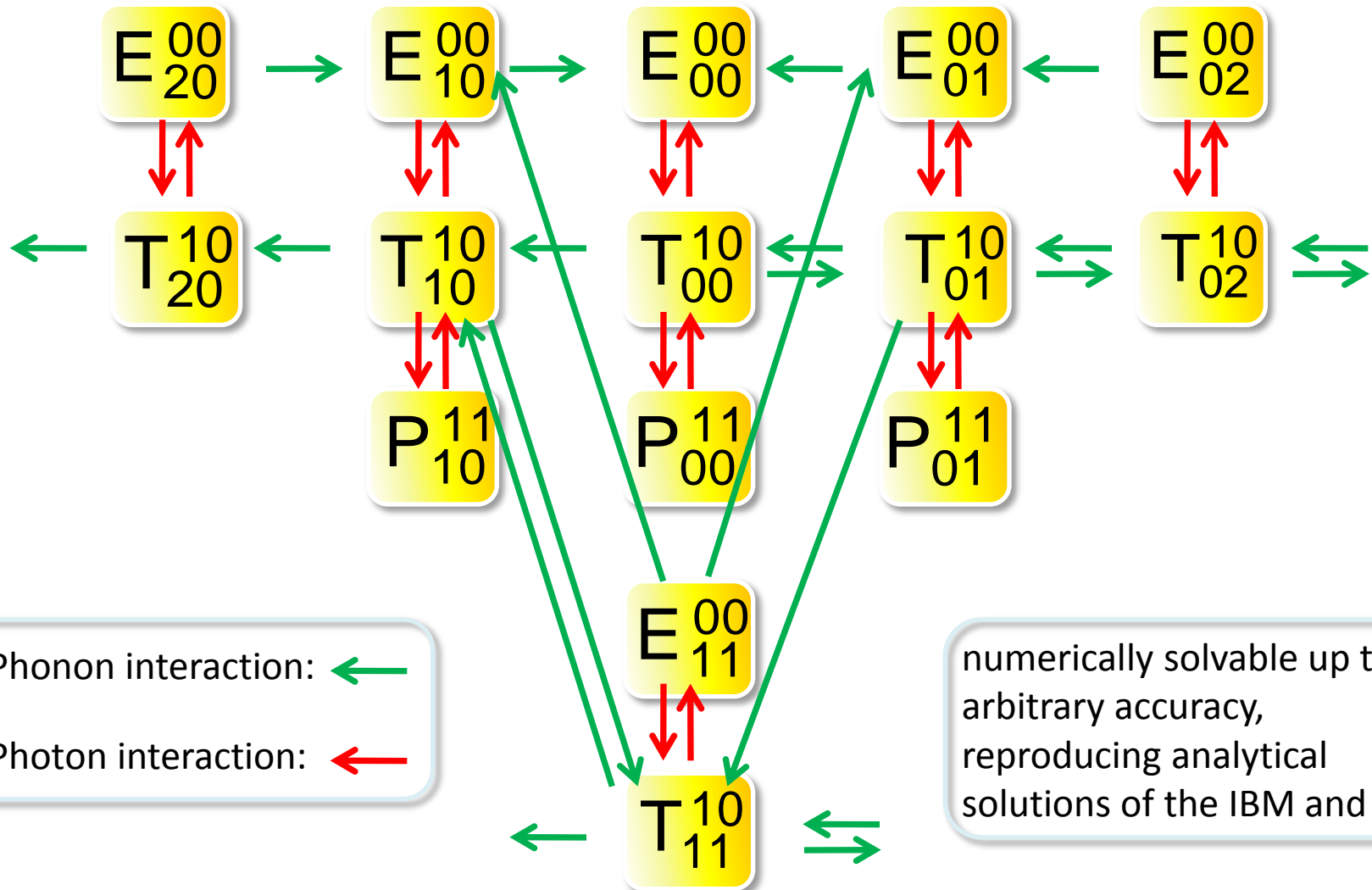


Photon interaction: ←

numerically solvable up to arbitrary accuracy, reproducing analytical solutions of the IBM and JCM

General set of equations of motion

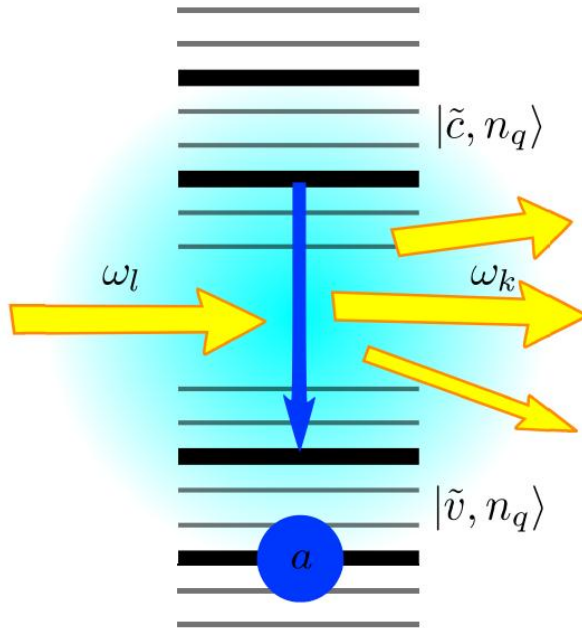
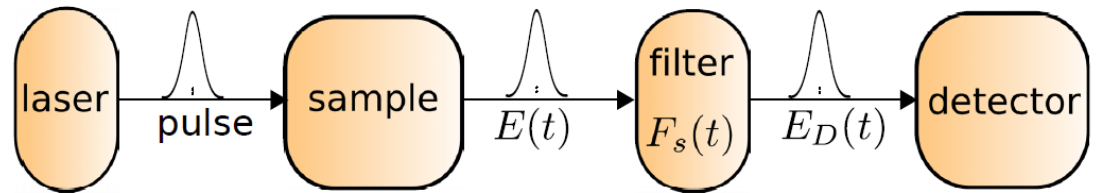
For example, in the case of LO-phonon assisted vacuum Rabi oscillations ($E_{00}^{11} = 0$):



(ii) quantum dot as a two-level system

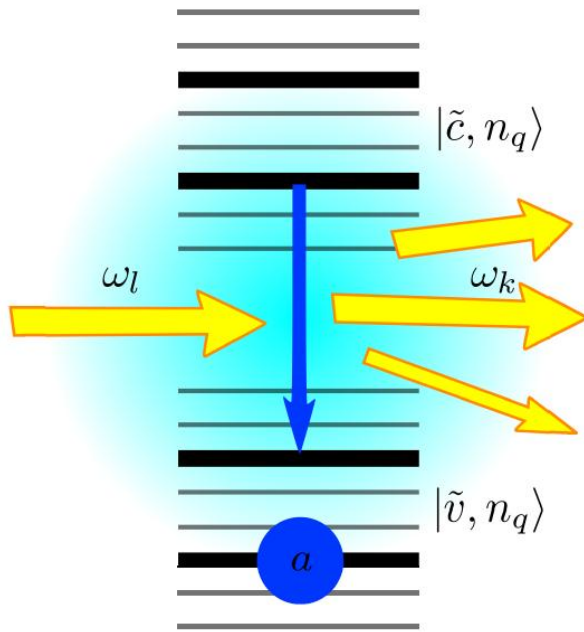
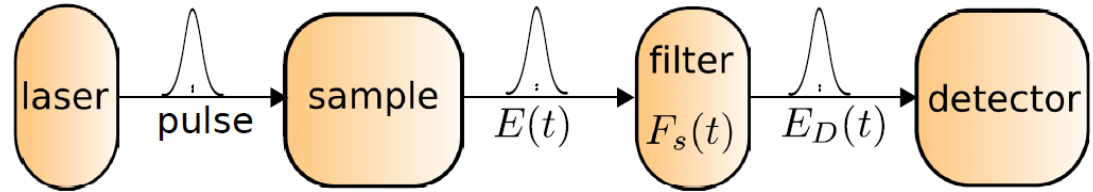
- Time-resolved phonon-assisted Mollow triplet
- Proposal for a phonon laser
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Strong excitation:

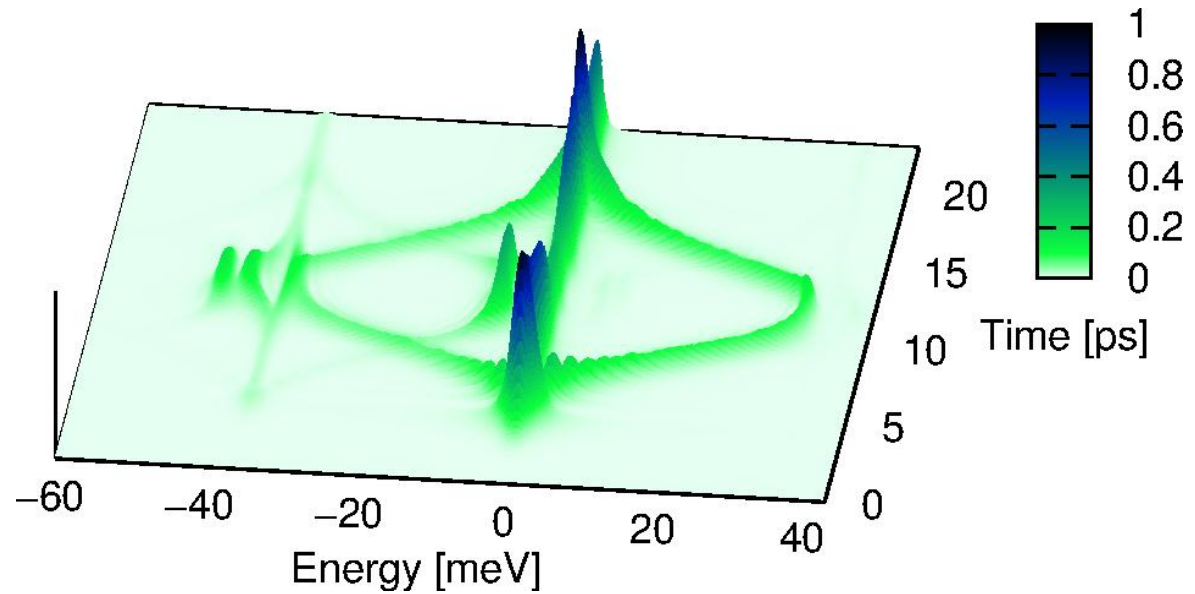


(b) strong excitation

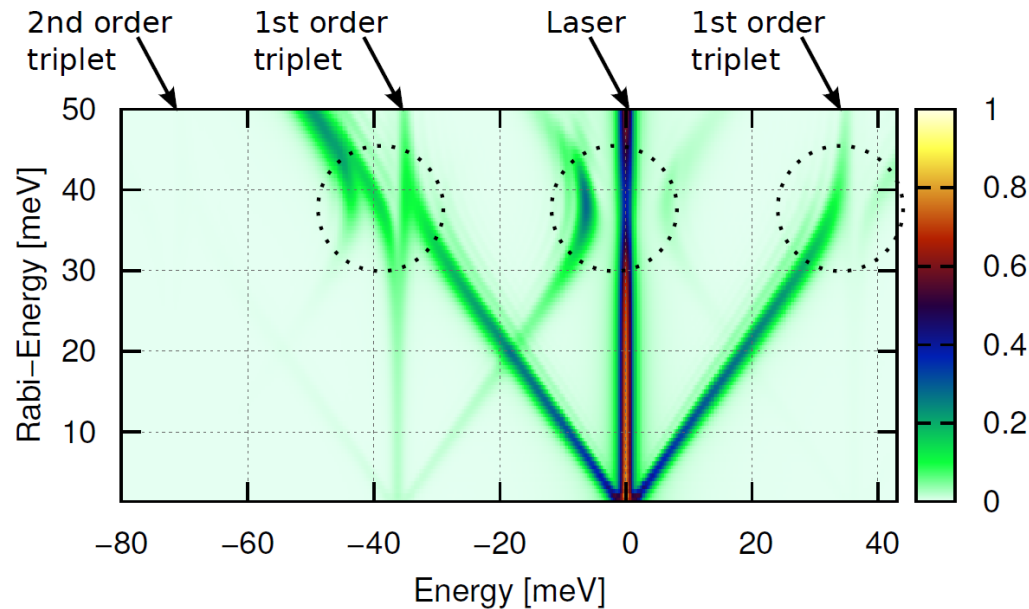
Strong excitation:



(b) strong excitation



Phonon coupling strength via anti-crossing



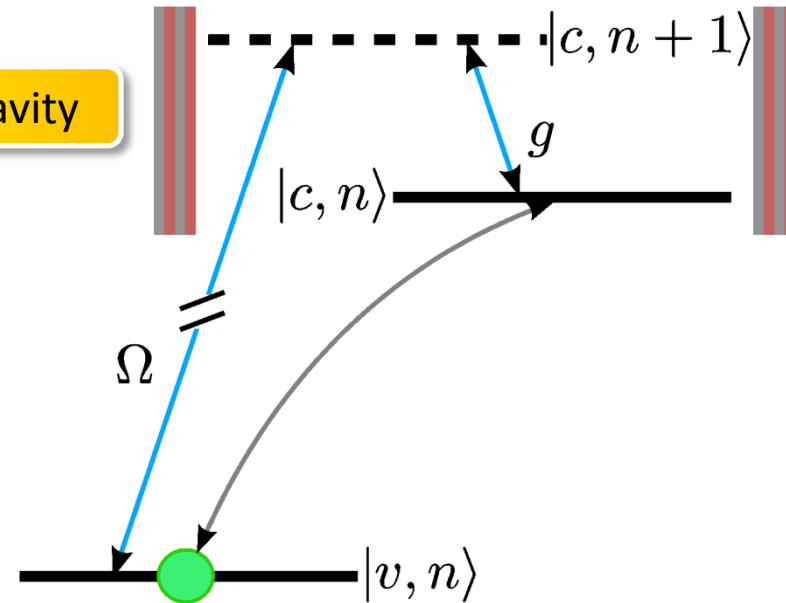
- ❑ Spectrum shows the usual Mollow triplet and phonon-assisted Mollow triplets
- ❑ Additional anticrossings, when the Rabi-energy matches the phonon energy (Here 36.4 meV for InGaAs/GaAs-QD)
- ❑ These anti-crossings scale with the electron-phonon coupling strength

(ii) quantum dot as a two-level system

- Time-resolved phonon-assisted Mollow triplet
- Proposal for a phonon laser**
- Photon-loss and induced quantum feedback

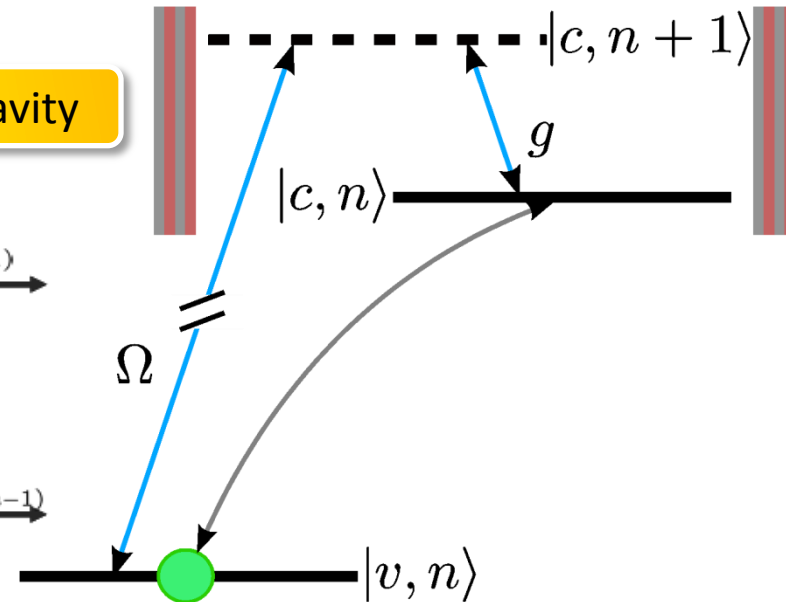
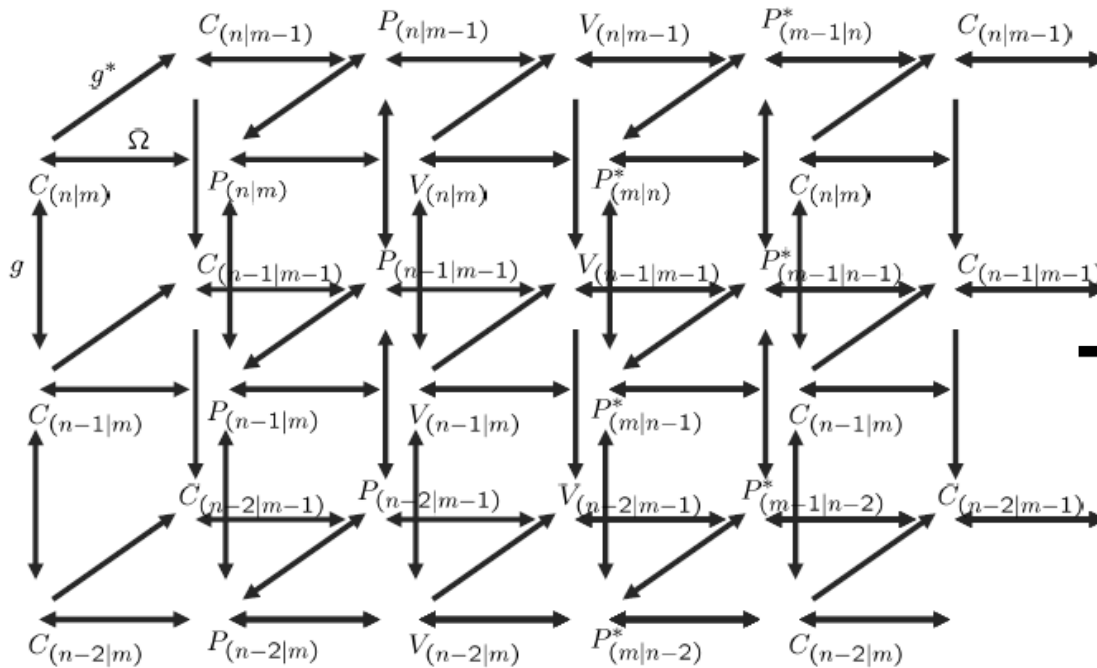
Proposal for a phonon laser

Non-resonant excited 2-level system in an acoustic cavity



Proposal for a phonon laser

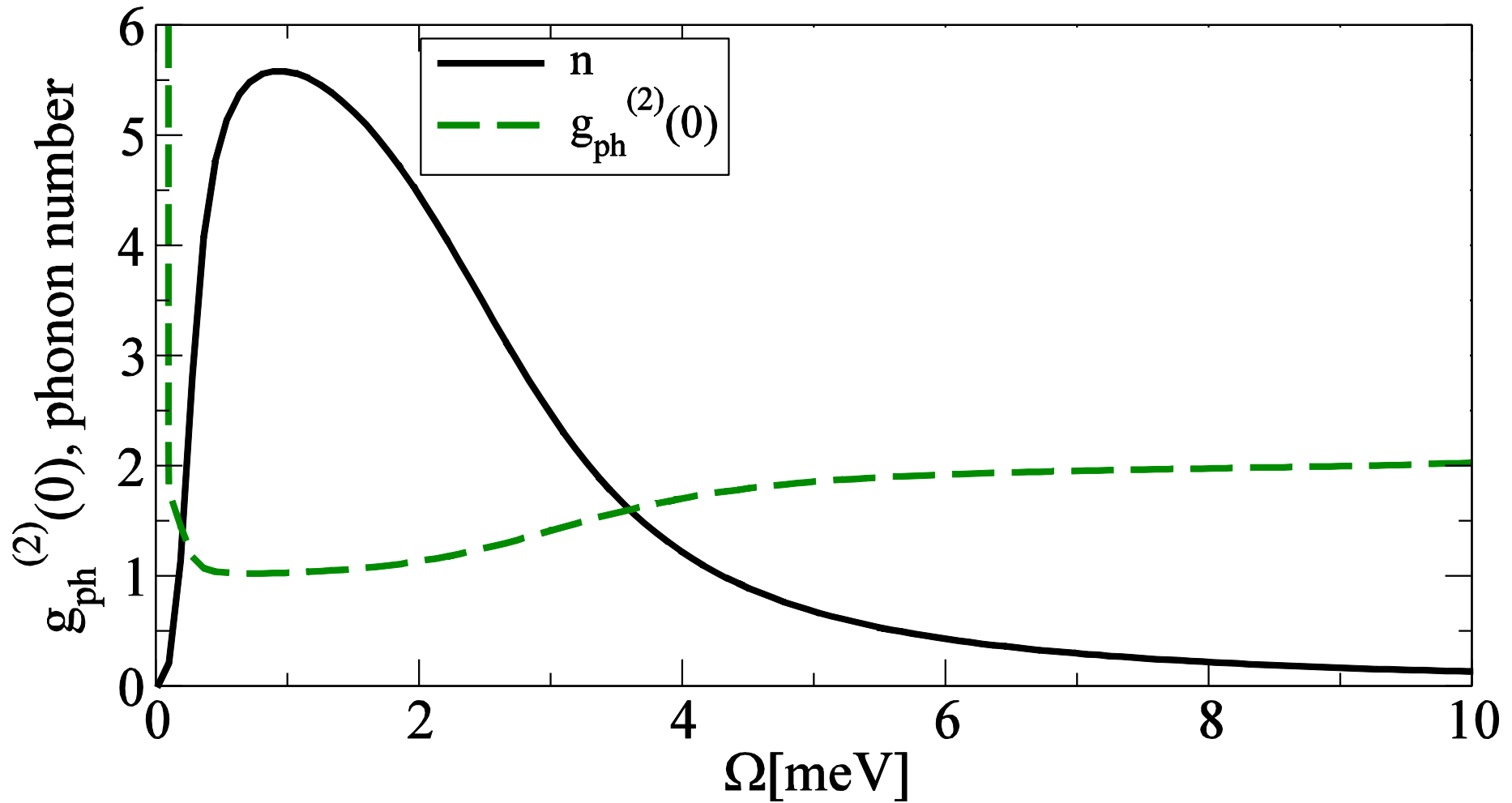
Non-resonant excited 2-level system in an acoustic cavity



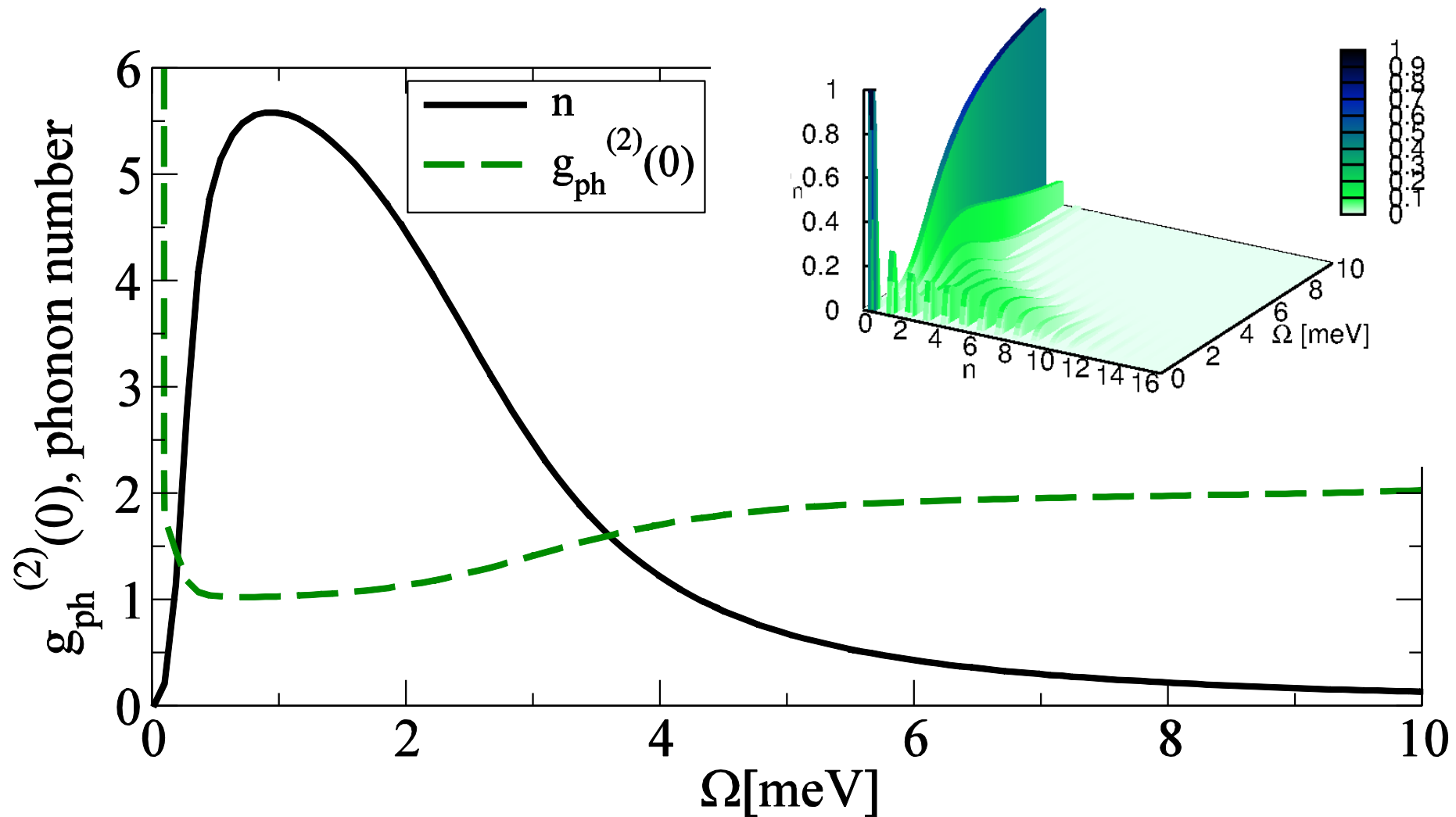
High orders of phonon operators become important ^{1,2,3}

¹PRL **104**, 156801 (2010), ²PSS(b) 248, **872** (2011), ³ submitted (2012)

Generation of coherent phonons



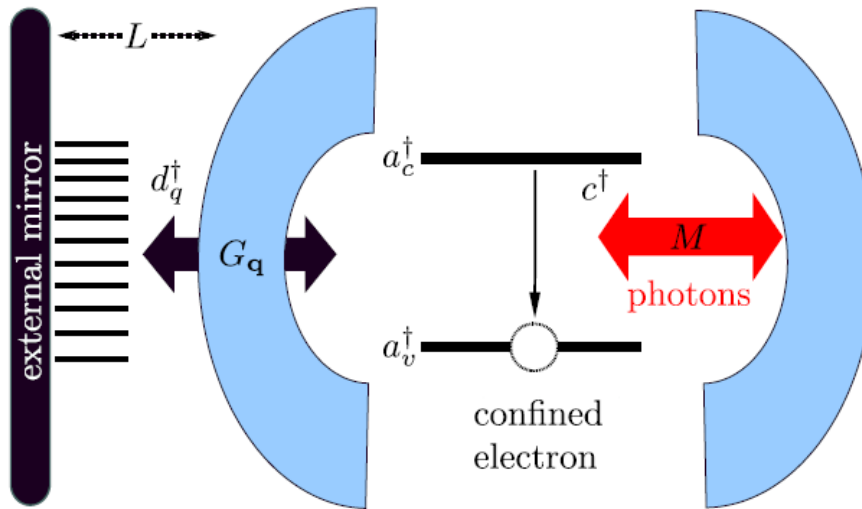
Generation of coherent phonons



(ii) quantum dot as a two-level system

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Photon-loss induced quantum feedback



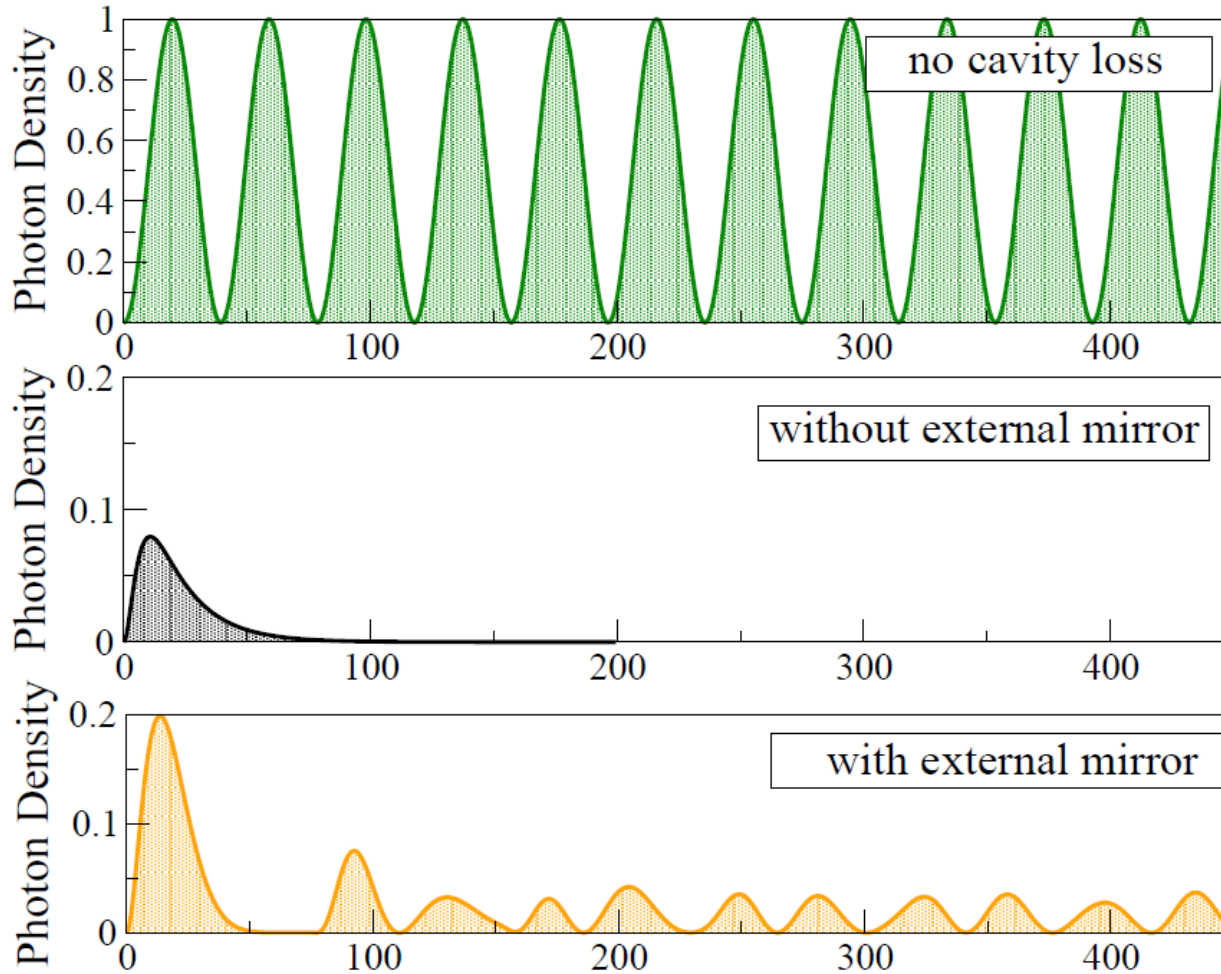
Set-up for quantum feedback

$$G_q = G \sin(q L)$$

External mirror shapes the mode continuum in front of the mirror to introduce a delay effect¹

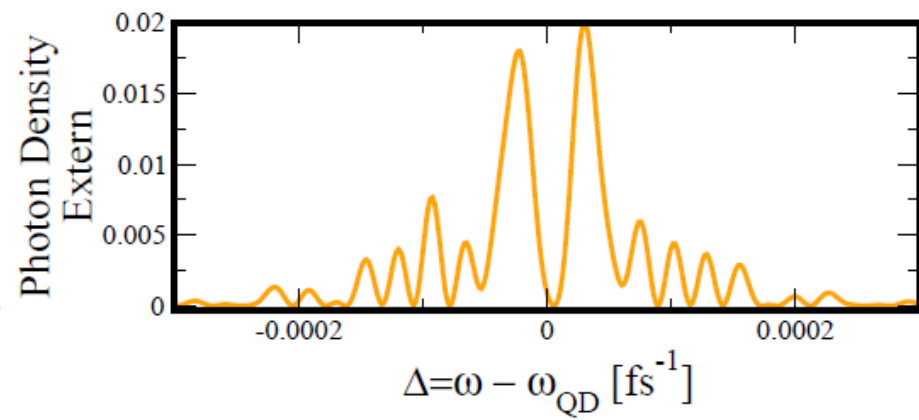
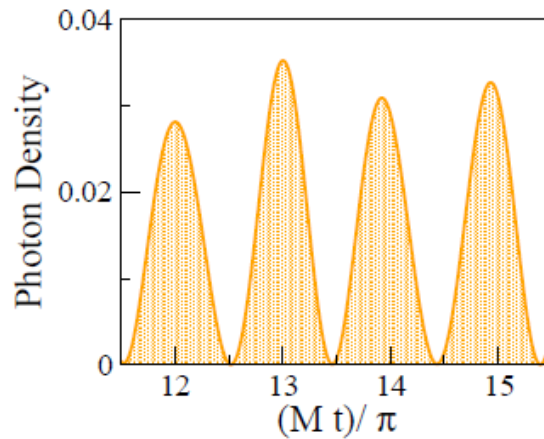
¹ in preparation (2012)

Photon-loss induced quantum feedback



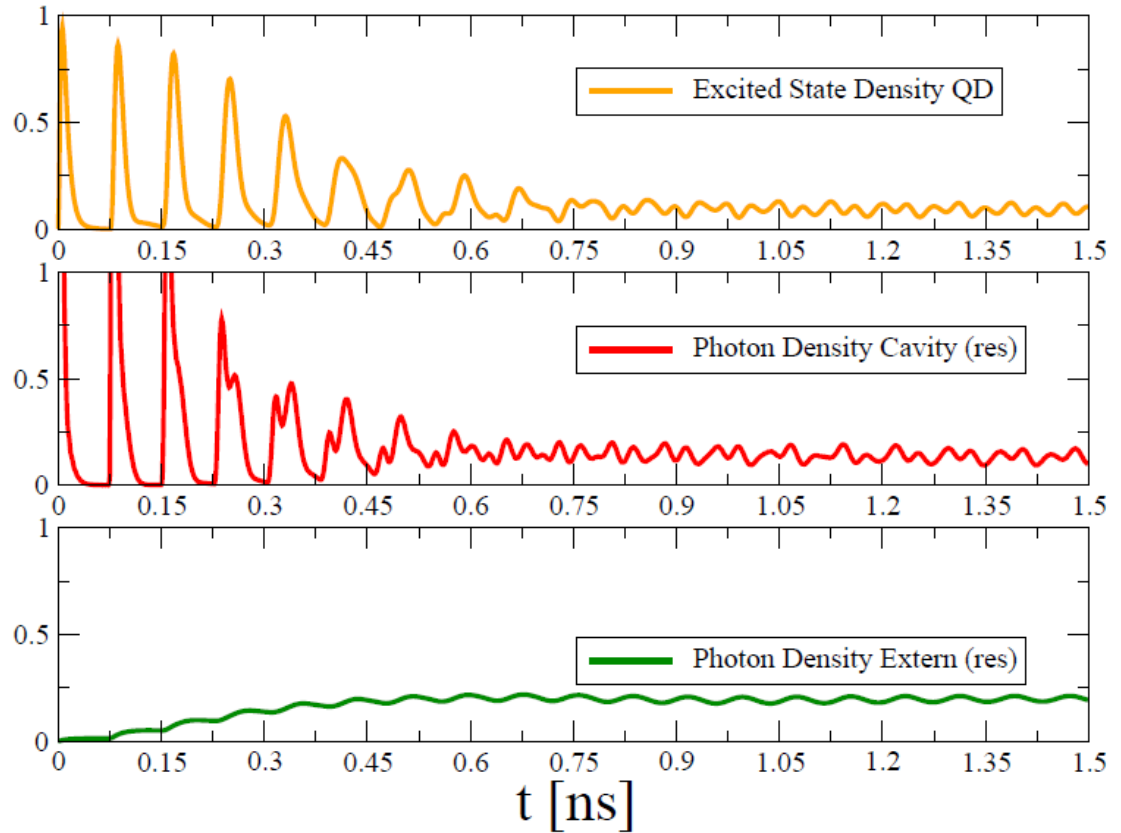
Photon-loss induced quantum feedback

External mirror shapes the mode continuum in front of the mirror to introduce a delay effect¹



¹ in preparation (2012)

Photon-loss induced quantum feedback



Classical limit¹:

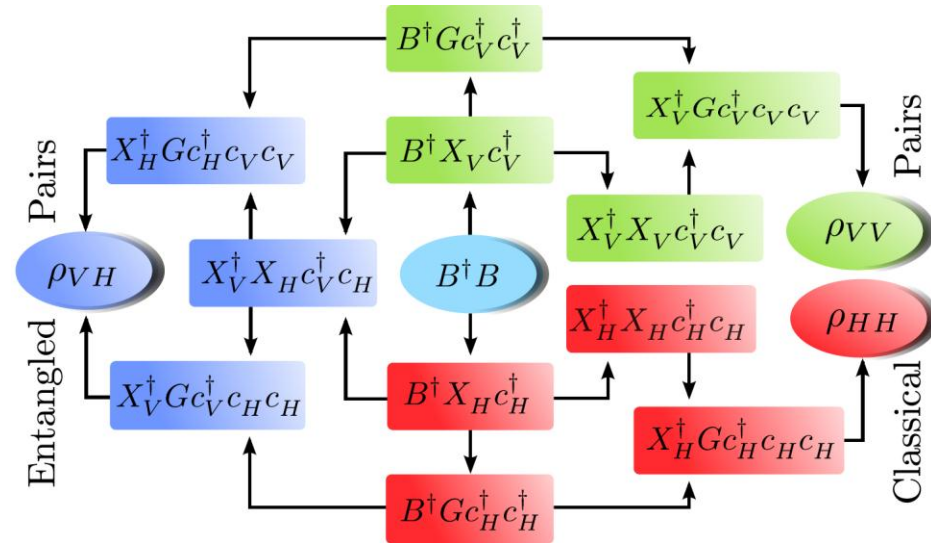
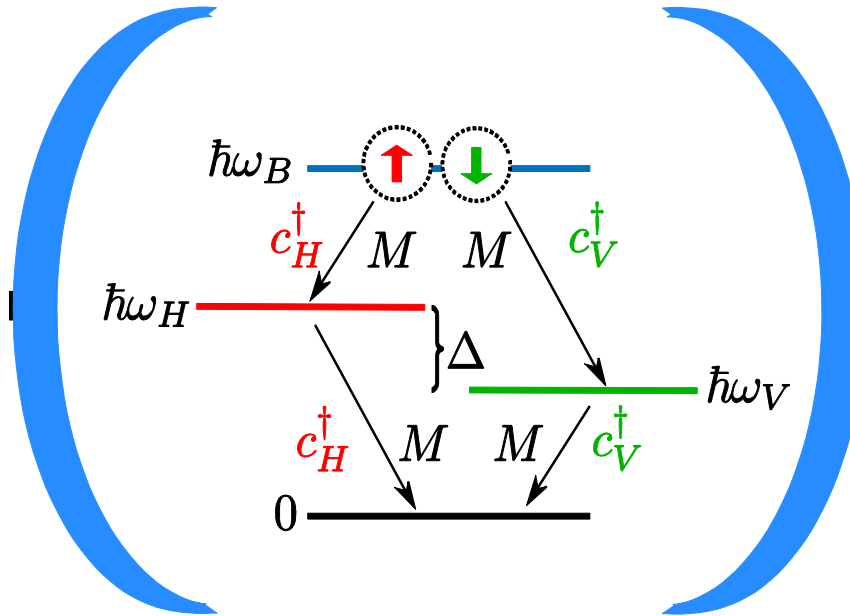
$$\langle a_c^\dagger a_c c^\dagger c \rangle \approx \langle a_c^\dagger a_c \rangle \langle c^\dagger c \rangle$$

¹ in preparation (2012)

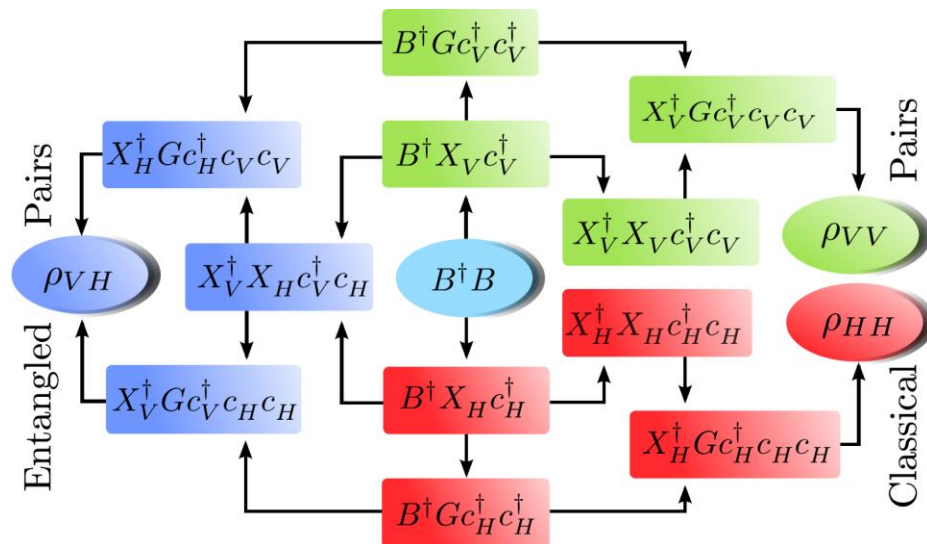
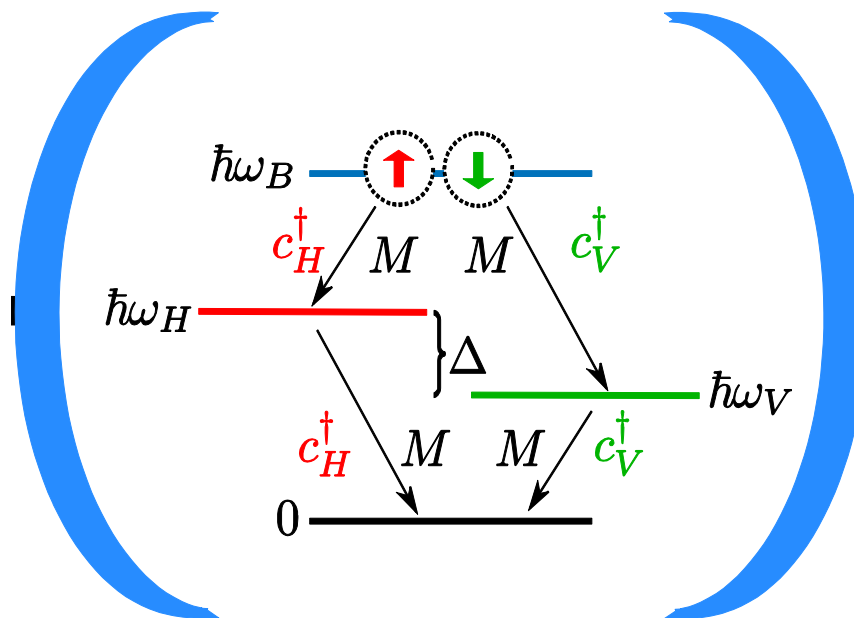
(iii) quantum dot as a four-level system

- Entangled photons: Pure dephasing does not matter
- Entangled photons: Multi-phonon scattering beyond 70K
- Strongly coupled cavity-QED: Crosscorrelation

Generation of entangled photon pairs via biexciton cascade



Generation of entangled photon pairs via biexciton cascade

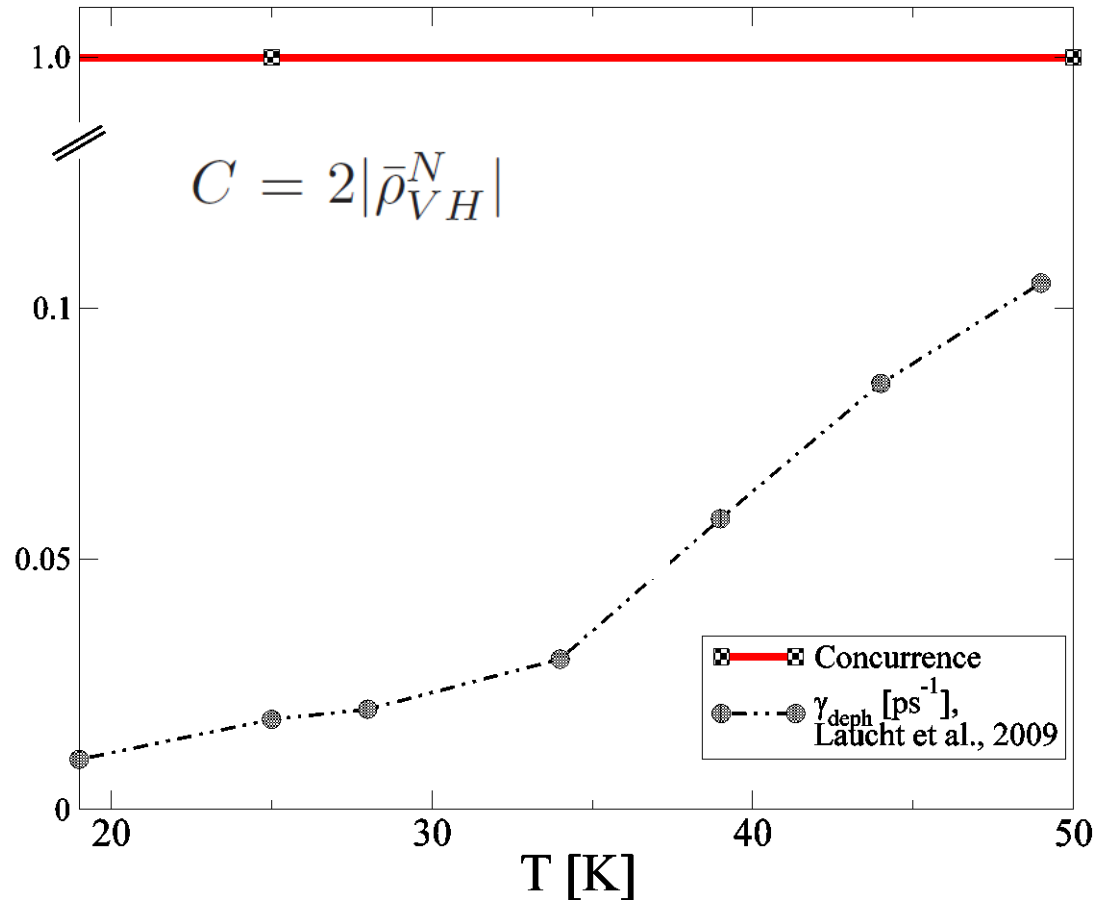


Analytical solvable in the adiabatic limit¹:

$$C = 2|\bar{\rho}_{VH}^N|$$

$$\bar{\rho}_{VH} = \frac{8M^4 [2/(\kappa_X - 2i\Delta) + 1/(\kappa_{GB} - i\Delta)]}{(\kappa_{GX} - 2i\Delta)(\kappa_{XB} - i\Delta)(\kappa_G - 2i\Delta)(\kappa_B - 2i\Delta)}$$

Generation of entangled photon pairs via biexciton cascade



Generation of entangled photon pairs via biexciton cascade

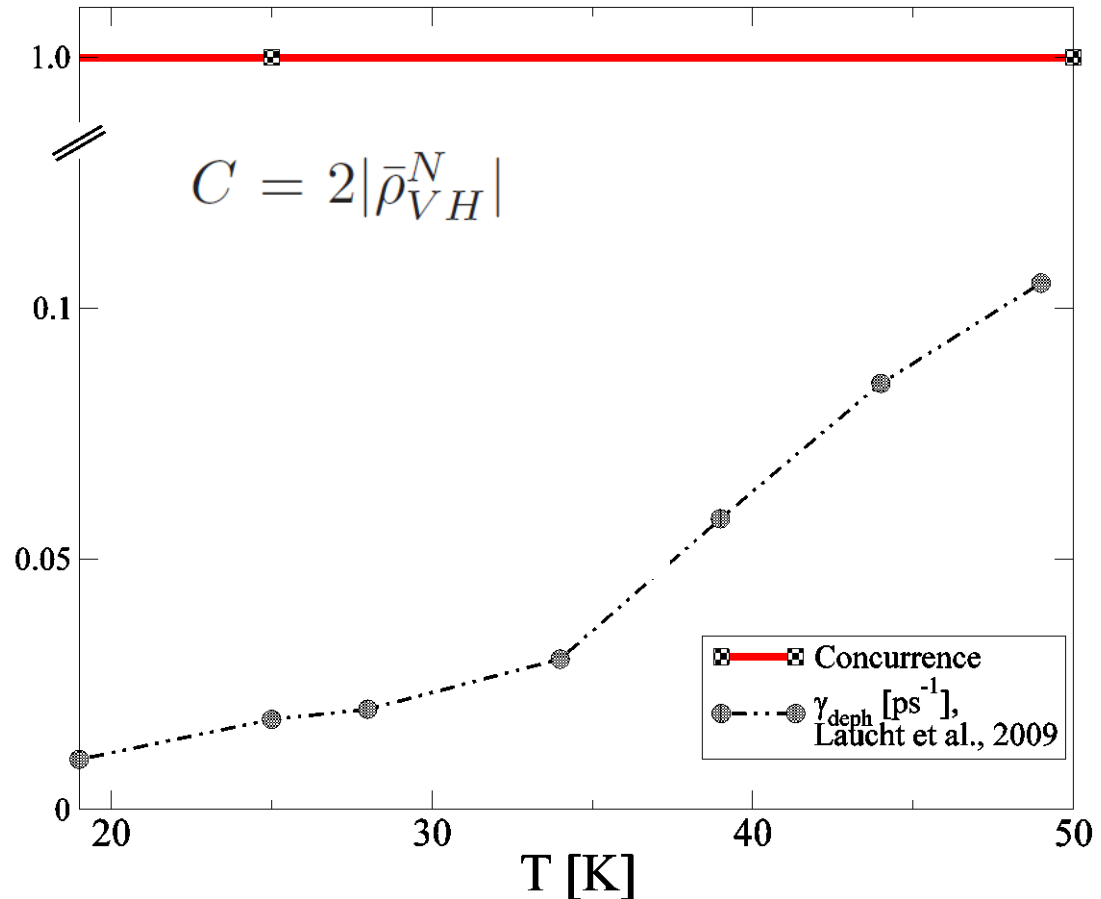
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Bayreuth: Seminar SS 2012

For typical dephasing constants, in semiconductor quantum dot cavity-QED, the degree is not affected by pure dephasing mechanism¹



No impact if the detuning is zero


¹PRB **84**, 075328 (2011)

(iii) quantum dot as a four-level system

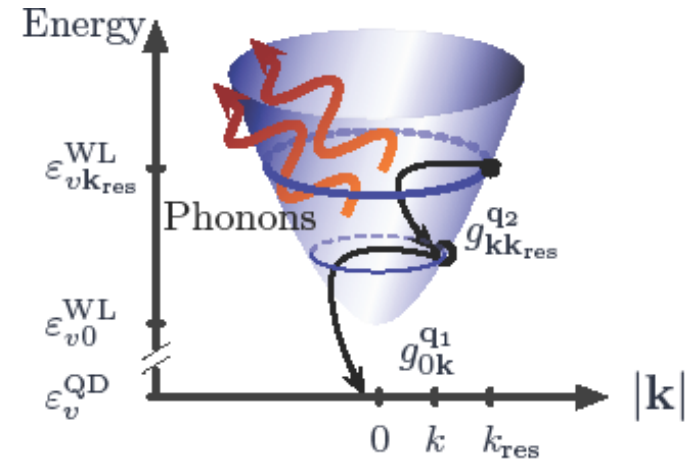
- Entangled photons: Pure dephasing does not matter
- Entangled photons: Multi-phonon scattering beyond 70K**
- Strongly coupled cavity-QED: Crosscorrelation

Temperature dependent degree of entanglement

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Bayreuth: Seminar SS 2012

- ❑ In an effective Hamiltonian approach a higher order Markovian process is assumed¹
- ❑ Multiphonon processes attack the generation of polarization entangled photons²:



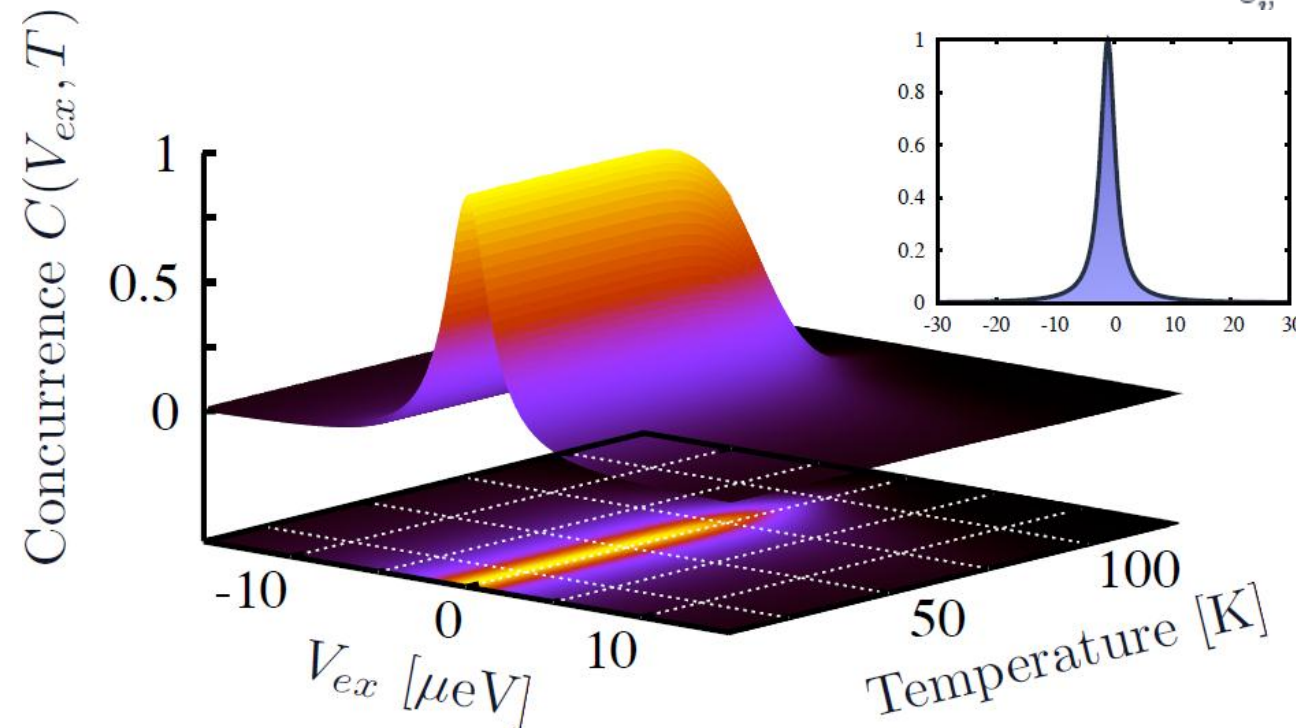
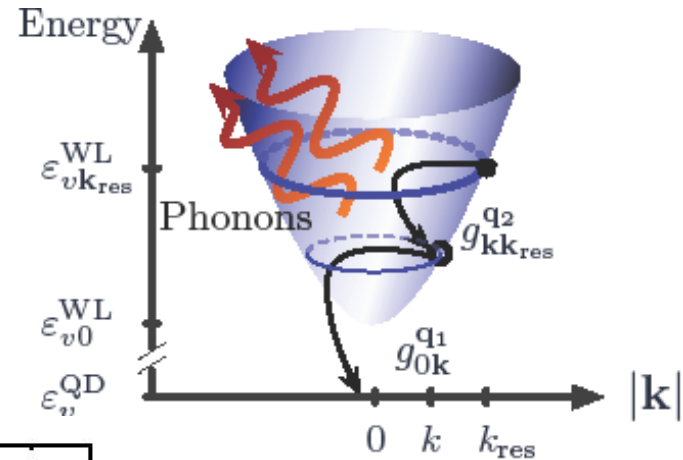
¹PSSB **247**, 809 (2010), ²PRB **81**, 195319 (2010)

Temperature dependent degree of entanglement

Slide: 47

Bayreuth: Seminar SS 2012

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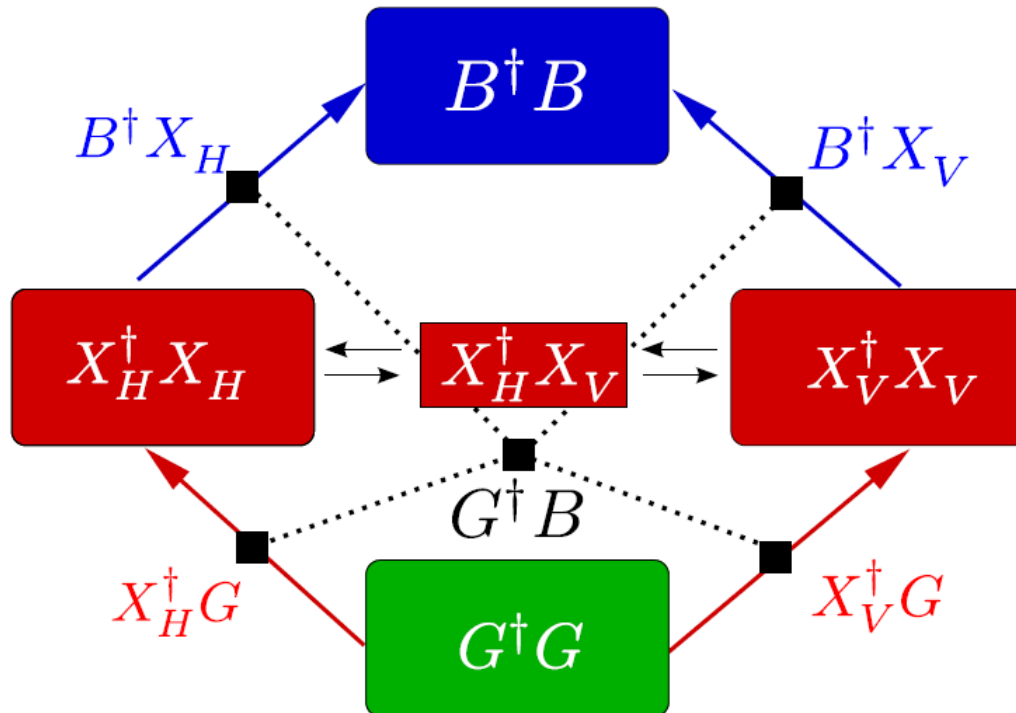
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(iii) quantum dot as a four-level system

- Entangled photons: Pure dephasing does not matter
- Entangled photons: Multi-phonon scattering beyond 70K
- Strongly coupled cavity-QED: Crosscorrelation**

Strongly coupled cavity-QED:

- Four-level system strongly coupled to cavity mode¹
- Investigation of entanglement dynamics and cross-correlation dynamics for exciton-lifetimes


¹in preparation (2012)

Strongly coupled cavity-QED:

- Example for an equation of motion¹
- Inclusion of coherent and incoherent excitation

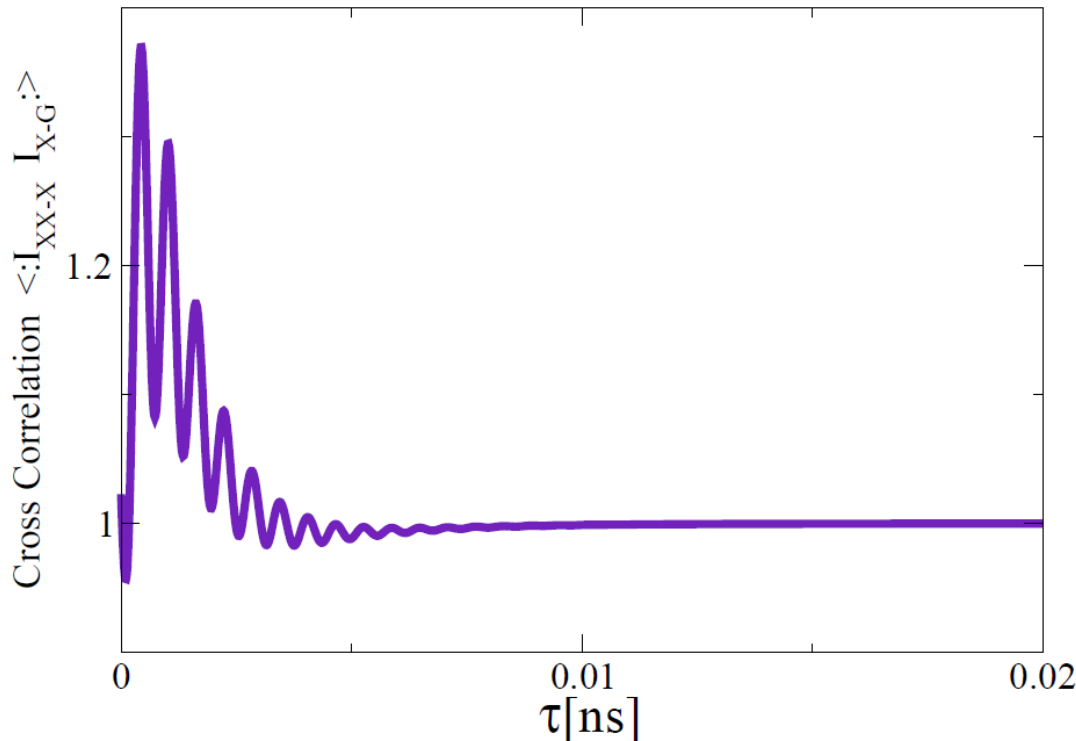
$$\begin{aligned}
 & \partial_t \langle B^\dagger B H^{m,n} V^{p,q} \rangle \\
 &= i \left[(m - n) \omega_H^0 + (p - q) \omega_V^0 + i\kappa(m + n + p + q) \right] \langle B^\dagger B H^{m,n} V^{p,q} \rangle \\
 & \quad - iM \langle X_H^\dagger B H^{m+1,n} V^{p,q} \rangle + iM \langle X_V^\dagger B H^{m,n} V^{p+1,q} \rangle \\
 & \quad + iM \langle B^\dagger X_H H^{m,n+1} V^{p,q} \rangle - iM \langle B^\dagger X_V H^{m,n} V^{p,q+1} \rangle \\
 & \quad - i\Omega_H(t) \langle X_H^\dagger B H^{m,n} V^{p,q} \rangle + i\Omega_V(t) \langle X_V^\dagger B H^{m,n} V^{p,q} \rangle \\
 & \quad + i\Omega_H^*(t) \langle B^\dagger X_H H^{m,n} V^{p,q} \rangle - i\Omega_V^*(t) \langle B^\dagger X_V H^{m,n} V^{p,q} \rangle
 \end{aligned}$$

Strongly coupled cavity-QED:

- Investigation of entanglement dynamics and cross-correlation dynamics for exciton-lifetimes

- Tau-dependence of cross-correlations

$$g^{(2)}(t, \tau) = \frac{\langle c_{XX}^\dagger(t) c_X^\dagger(t + \tau) c_X(t + \tau) c_{XX}(t) \rangle}{\langle c_{XX}^\dagger c_{XX} \rangle(t) \langle c_X^\dagger c_X \rangle(t + \tau)}$$

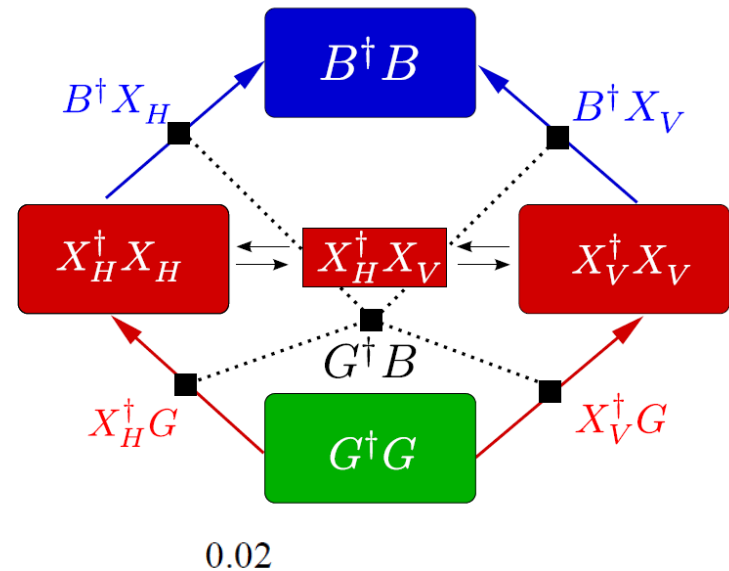
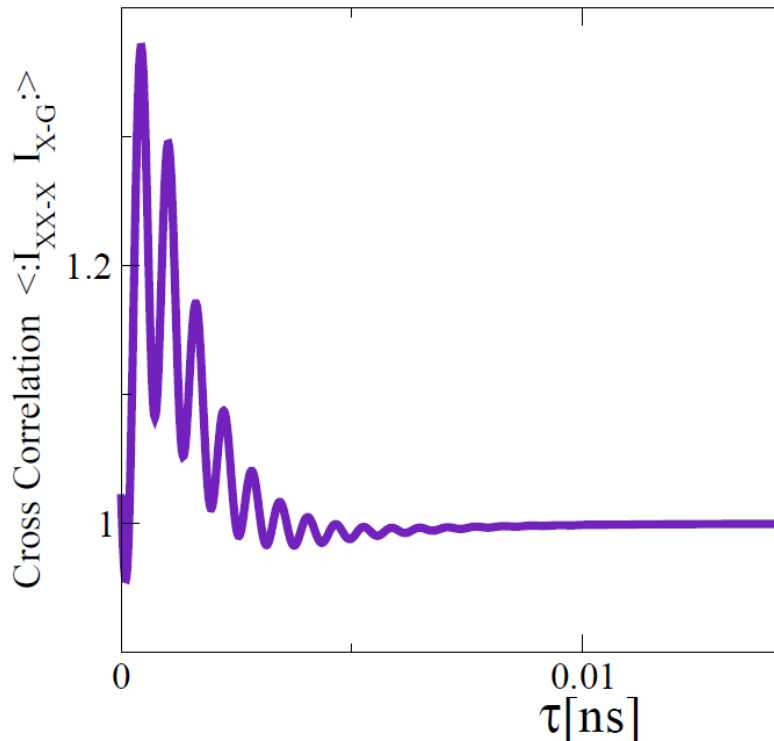


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(iv) conclusion

Conclusion

$$H = H_{\text{el}} + H_{\text{phonon}} + H_{\text{photon}} + H_{\text{laser}}$$

$$H_{\text{el}} = \hbar \sum_i \omega_i a_i^\dagger a_i + \hbar \sum_{ijlm} V_{lm}^{ij} a_i^\dagger a_j^\dagger a_l a_m$$

$$H_{\text{phonon}} = \hbar \sum_{\mathbf{q}} \omega_{\mathbf{q}} b_{\mathbf{q}}^\dagger b_{\mathbf{q}} + \hbar \sum_{i,j,\mathbf{q}} g_{\mathbf{q}}^{ij} a_i^\dagger a_j b_{\mathbf{q}}^\dagger + \text{H.c.}$$

$$H_{\text{photon}} = \hbar \sum_{\mathbf{k}} \omega_{\mathbf{k}} c_{\mathbf{k}}^\dagger c_{\mathbf{k}} + \hbar \sum_{i,j,\mathbf{k}} M_{\mathbf{k}}^{ij} a_i^\dagger a_j c_{\mathbf{k}}^\dagger + \text{H.c.}$$

$$H_{\text{laser}} = \hbar \sum_{i,j} \Omega^{ij} a_i^\dagger a_j + \text{H.c.}$$

- Electron-electron interaction: enhanced Pauli-blocking
- Electrical pumping
- Förster coupled QD: solid-state qubits

Conclusion

$$H = H_{\text{el}} + H_{\text{phonon}} + H_{\text{photon}} + H_{\text{laser}}$$

$$H_{\text{el}} = \hbar \sum_i \omega_i a_i^\dagger a_i + \hbar \sum_{ijlm} V_{lm}^{ij} a_i^\dagger a_j^\dagger a_l a_m$$

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$$H_{\text{laser}} = \hbar \sum_{i,j} \Omega^{ij} a_i^\dagger a_j + \text{H.c.}$$

- LO-phonon enhanced anti-bunching
- LA-phonon enhanced collapse and revival phenomenon
- Generation of coherent phonons in acoustic cavities

Thank you for your attention !!